UHF power LDMOS transistor Rev. 2 — 30 August 2016

AMPLEON

Product data sheet

Product profile 1.

1.1 General description

A 750 W LDMOS RF power transistor for asymmetrical broadcast Doherty transmitter applications which operates at 150 W DVB-T average power. The excellent ruggedness of this device makes it ideal for digital and analog transmitter applications.

Application information Table 1.

RF performance at V_{DS} = 50 V in an asymmetrical Doherty application.

Test signal	f	P _{L(AV)}	Gp	η _D	IMD _{shidr}	PAR
	(MHz)	(W)	(dB)	(%)	(dBc)	(dB)
DVB-T (8k OFDM)	470 to 608	150	17	52	-38	8 <u>[1]</u>
	600 to 700	150	17	50	-38	8 <u>[1]</u>
	650 to 790	150	15	49	-38	8 <u>[1]</u>

^[1] PAR (of output signal) at 0.01 % probability on CCDF; PAR of input signal = 9.5 dB at 0.01 % probability on CCDF.

1.2 Features and benefits

- Designed for asymmetric Doherty operation
- Very high efficiency enabling air cooled high power transmitters
- Integrated ESD protection
- Excellent ruggedness
- High power gain
- Excellent reliability
- Easy power control
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- Broadcast transmitter applications in the UHF band
- Digital broadcasting

2. Pinning information

Table 2. Pinning

Description	Simplified outline	Graphic symbol
SOT539A)		
drain1 (peak)		
drain2 (main)	1 2	1
gate1 (peak)	5	
gate2 (main)	3 4	3——5
source	[1]	4—
		2 sym117
(SOT539B)		
drain1 (peak)		
drain2 (main)	1 2	1
gate1 (peak)	5	
gate2 (main)	3 4	3 — 5
source	[1]	2 sym117
	drain1 (peak) drain2 (main) gate1 (peak) gate2 (main) source (SOT539B) drain1 (peak) drain2 (main) gate1 (peak) gate2 (main)	drain1 (peak) drain2 (main) gate1 (peak) gate2 (main) source (SOT539B) drain1 (peak) drain2 (main) gate1 (peak) gate2 (main)

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	Package			
	Name	Description	Version		
BLF888E	-	flanged balanced ceramic package; 2 mounting holes; 4 leads	SOT539A		
BLF888ES	-	earless flanged balanced ceramic package; 4 leads	SOT539B		

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS(amp)main}	main amplifier drain-source voltage		-	104	V
$V_{DS(amp)peak}$	peak amplifier drain-source voltage		-	120	٧
$V_{\text{GS}(\text{amp})\text{main}}$	main amplifier gate-source voltage		-0.5	+11	٧
$V_{GS(amp)peak}$	peak amplifier gate-source voltage		-6	+11	٧
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

^[1] Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-c)}	thermal resistance from junction to case	$T_{case} = 90 ^{\circ}\text{C}; V_{DS} = 50 \text{V};$ [1] $I_{DS} = 3 \text{A (main)}; I_{DS} = 0 \text{A (peak)}$	0.29	K/W
		$T_{case} = 90 ^{\circ}\text{C}; V_{DS} = 50 \text{V};$ $P_L = 150 \text{W}; PAR = 8 \text{dB}$	0.19	K/W

- [1] Measured under DC test conditions, with peak section off.
- [2] Measured in an ultra-wide Doherty application, using DVB-T (8k OFDM) signal, PAR (of output signal) at 0.01 % probability on CCDF; PAR of input signal = 9.5 dB at 0.01 % probability on CCDF.

6. Characteristics

Table 6. DC characteristics

 T_i = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main dev	rice					
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.4 \text{ mA}$	104	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 240 mA	1.25	1.75	2.25	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 50 V	-	-	2.8	μА
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	38	-	Α
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V	-	-	280	nA
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 8.5 \text{ A}$	-	120	-	mΩ
Peak dev	rice					
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 3.6 \text{ mA}$	125	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 360 mA	1.33	1.83	2.33	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 50 V	-	-	2.8	μА
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	57	-	Α
I _{GSS}	gate leakage current	V _{GS} = 10 V; V _{DS} = 0 V	-	-	280	nA
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 12.6 \text{ A}$	-	90	-	mΩ

Table 7. AC characteristics

 T_i = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main device						
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	210	-	pF
C _{oss}	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	67	-	pF
C _{rss}	reverse transfer capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	1.35	-	pF

UHF power LDMOS transistor

Table 7. AC characteristics ...continued

 T_i = 25 °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Peak device						
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	315	-	pF
Coss	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	105	-	pF
C _{rss}	reverse transfer capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	1.5	-	pF

Table 8. RF characteristics

RF characteristics in Ampleon production test circuit, $T_{case} = 25 \, ^{\circ}\text{C}$; unless otherwise specified.

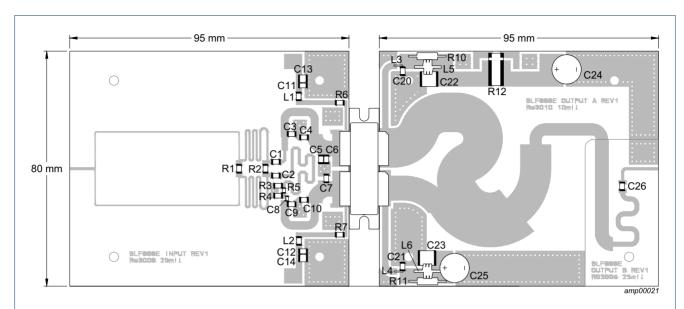
	• •	, 6466				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
DVB-T (8	Bk OFDM), Doherty operation					
V_{DS}	drain-source voltage		-	50	-	V
I_{Dq}	quiescent drain current	peak section: $V_{GS} = 1.3 \text{ V}$ below $V_{GS(th)}$ (peak)	-	600	-	mA
$P_{L(AV)}$	average output power	f = 550 MHz	-	150	-	W
Gp	power gain	f = 550 MHz	15.8	17	-	dB
η _D	drain efficiency	f = 550 MHz	48	52	-	%
PAR	peak-to-average ratio	f = 550 MHz	7.2	7.8	-	dB

7. Test information

7.1 Ruggedness in Doherty operation

The BLF888E and BLF888ES are capable of withstanding a load mismatch corresponding to VSWR \geq 40 : 1 through all phases under the following conditions: V_{DS} = 50 V; f = 550 MHz at rated load power.

7.2 Test circuit



Printed-Circuit Board (PCB): Rogers 3006; ε_r = 6.5 F/m; height = 0.635 mm; Cu (top/bottom metalization); thickness copper plating = 29.6 μ m; Rogers 3010: ε_r = 10 F/m; height = 0.254 mm

See Table 9 for a list of components.

Fig 1. Component layout for production RF test circuit

Table 9. List of components For test circuit see Figure 1.

Component	Description	Value		Remarks
C1, C2	multilayer ceramic chip capacitor	51 pF	[1]	ATC 100B
C3	multilayer ceramic chip capacitor	11 pF	[1]	ATC 100B
C4	multilayer ceramic chip capacitor	13 pF	[1]	ATC 100B
C5, C6	multilayer ceramic chip capacitor	24 pF	[1]	ATC 100B
C7	multilayer ceramic chip capacitor	33 pF	[1]	ATC 100B
C8	multilayer ceramic chip capacitor	51 pF	[2]	ATC 100A
C9	multilayer ceramic chip capacitor	12 pF	[1]	ATC 100B
C10	multilayer ceramic chip capacitor	20 pF	[1]	ATC 100B
C11, C12	multilayer ceramic chip capacitor	43 pF	[1]	ATC 100B
C13, C14	multilayer ceramic chip capacitor	4.7 μF		
C20, C21	electrolytic capacitor	100 pF	[1]	ATC 100B
C22, C23	multilayer ceramic chip capacitor	4.7 μF, 100 V		
C25, C25	electrolytic capacitor	470 μF, 63 V		
C26	multilayer ceramic chip capacitor	47 pF	[1]	ATC 100B
L1, L2	inductor	10 nH		Coilcraft
L3, L4	inductor	0.5 turn, D = 2 mm, d = 1mm		
L5, L6	inductor	1 turn, D = 5 mm, d = 1mm		
R1	chip resistor	90 Ω		

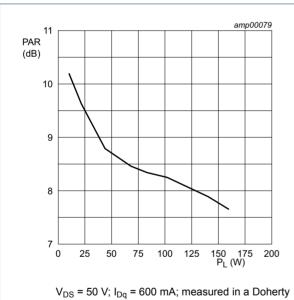
Table 9. List of components ...continued For test circuit see Figure 1.

Component	Description	Value	Remarks
R2	chip resistor	265 Ω	
R3, R4	chip resistor	360 Ω	
R5	chip resistor	15 Ω	
R6	chip resistor	75 Ω	
R7	chip resistor	5 Ω	
R10, R11	wire resistor	1 Ω	
R12	shunt resistor	0.01 Ω	

- [1] American Technical Ceramics type 100B or capacitor of same quality
- [2] American Technical Ceramics type 100A or capacitor of same quality

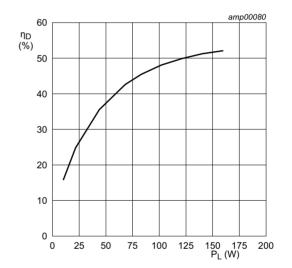
7.3 Graphical data

7.3.1 DVB-T in production test circuit



 $v_{DS} = 50 \text{ V}$; $v_{Dq} = 600 \text{ mA}$; measured in a Donerty production test circuit at 550 MHz.

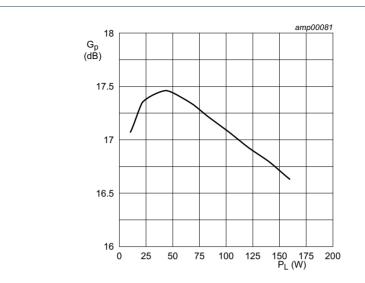
Fig 2. Peak-to-average power ratio as a function of output power; typical values



 V_{DS} = 50 V; I_{Dq} = 600 mA; measured in a Doherty production test circuit at 550 MHz.

Fig 3. Drain efficiency as a function of output power; typical values

UHF power LDMOS transistor



 V_{DS} = 50 V; I_{Dq} = 600 mA; measured in a Doherty production test circuit at 550 MHz.

Fig 4. Power gain as a function of output power; typical values

8. Package outline

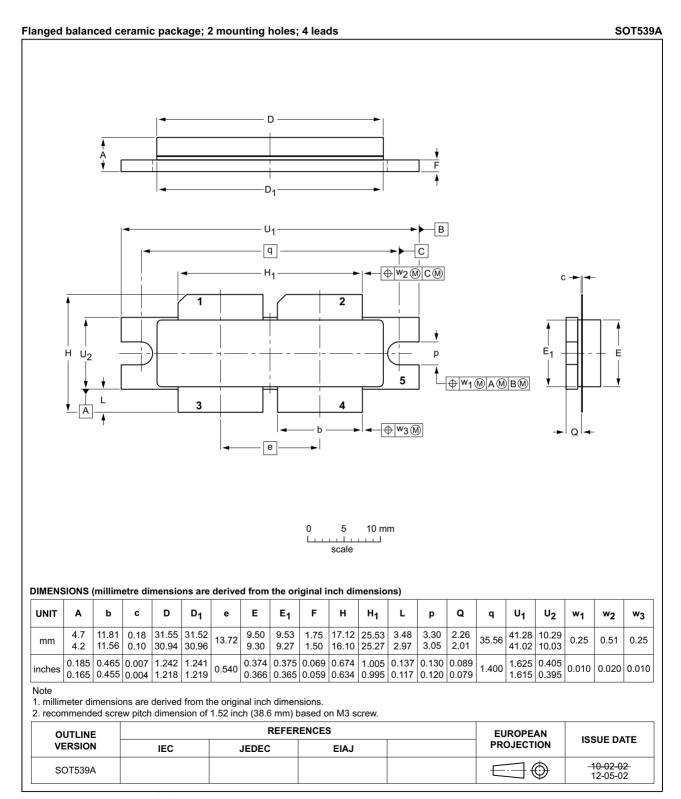


Fig 5. Package outline SOT539A

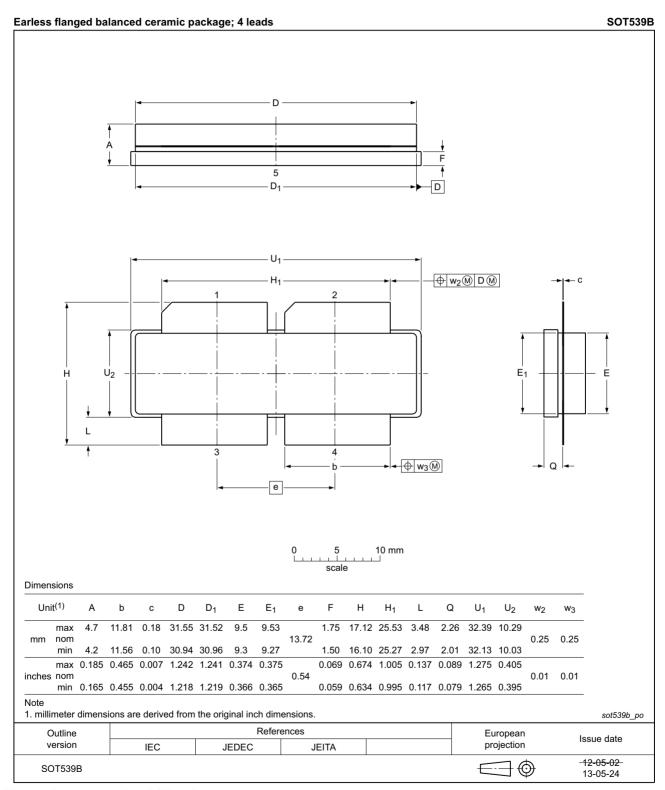


Fig 6. Package outline SOT539B

UHF power LDMOS transistor

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

10. Abbreviations

Table 10. Abbreviations

Acronym	Description
CCDF	Complementary Cumulative Distribution Function
DVB-T	Digital Video Broadcast - Terrestrial
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
OFDM	Orthogonal Frequency Division Multiplexing
PAR	Peak-to-Average Ratio
UHF	Ultra High Frequency
VSWR	Voltage Standing Wave Ratio

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLF888E_BLF888ES v.2	20160830	Product data sheet	-	BLF888E_BLF888ES v.1
Modifications:	Section 1.1 on page 1: section updated			
	• <u>Table 1 on page 1</u> : table updated			
	Section 1.2 on page 1: text second list item updated			
	<u>Table 5 on page 3</u> : table updated			
	• <u>Table 6 on page 3</u> : table updated			
	 Table 8 on page 4: table updated Section 7.1 on page 4: section updated Section 7.3 on page 6: section added 			
BLF888E_BLF888ES v.1	20160317	Objective data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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UHF power LDMOS transistor

14. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
2	Pinning information 2
3	Ordering information
4	Limiting values
5	Thermal characteristics 3
6	Characteristics 3
7	Test information 4
7.1	Ruggedness in Doherty operation 4
7.2	Test circuit
7.3	Graphical data 6
7.3.1	DVB-T in production test circuit 6
8	Package outline 8
9	Handling information 10
10	Abbreviations
11	Revision history 10
12	Legal information 11
12.1	Data sheet status
12.2	Definitions
12.3	Disclaimers
12.4	Licenses
12.5	Trademarks12
13	Contact information 12
14	Contents 13

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